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3-7-03

Docket No.: 8733.132.20-US (PATENT) *Q. Butler*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Joon-Young Yang

Application No.: 09/875,197

Group Art Unit: 2814

Filed: June 7, 2001

Examiner: S. Rao

For: METHOD OF FABRICATING A THIN FILM  
TRANSISTOR

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TECHNOLOGY CENTER 2800

PRELIMINARY AMENDMENT

Box RCE  
Commissioner for Patents  
Washington, DC 20231

Dear Sir:

In response to the Examiner's Final Office Action dated November 6, 2002 and Advisory Action dated February 12, 2003, and further to the attached Request for Continued Examination (RCE), please amend the above-identified application as follows.

In the Claims

Please **ADD** the following new claims:

41. (New) A method of fabricating a thin film transistor, comprising:

forming a gate insulating layer on an active layer;

forming a gate on the gate insulating layer;

forming an excited region in an exposed portion of the active layer by implanting hydrogen ions to the active layer by using the gate as a mask; and

forming an impurity region by heavily implanting impurity ions to said excited region